**Features:**

- n Isolated mounting base 3000V~
- n Solder joint technology with increased power cycling capability
- n Space and weight saving

**Typical Applications**

- n AC/DC Motor drives
- n Various rectifiers
- n DC supply for PWM inverter

| $V_{DSM}, V_{RSM}$ | $V_{DRM}, V_{RRM}$ | Type & Outline |
|--------------------|--------------------|----------------|
| 900V               | 800V               | MFC90-08-224H3 |
| 1100V              | 1000V              | MFC90-10-224H3 |
| 1300V              | 1200V              | MFC90-12-224H3 |
| 1500V              | 1400V              | MFC90-14-224H3 |
| 1700V              | 1600V              | MFC90-16-224H3 |
| 1900V              | 1800V              | MFC90-18-224H3 |

| SYMBOL                 | CHARACTERISTIC                             | TEST CONDITIONS  | $T_j(^{\circ}\text{C})$ | VALUE |      |      | UNIT                           |
|------------------------|--|--|-------------------------|-------|------|------|--------------------------------|
|                        |  |  |                         | Min   | Type | Max  |                                |
| $I_{T(AV)}$            | Mean on-state current                      | 180° half sine wave 50Hz<br>Single side cooled, $T_c=85^{\circ}\text{C}$ | 125                     |       |      | 90   | A                              |
| $I_{T(RMS)}$           | RMS on-state current                       |  | 125                     |       |      | 141  | A                              |
| $I_{DRM}$<br>$I_{RRM}$ | Repetitive peak current                    | at $V_{DRM}$<br>at $V_{RRM}$   | 125                     |       |      | 20   | mA                             |
| $I_{TSM}$              | Surge on-state current                     | 10ms half sine wave  | 125                     |       |      | 1.9  | kA                             |
| $I^2t$                 | $I^2t$ for fusing coordination             | $V_R=60\%V_{RRM}$  |                         |       |      | 18.1 | $\text{A}^2\text{s}\cdot 10^3$ |
| $V_{TO}$               | Threshold voltage                          |  | 125                     |       |      | 0.70 | V                              |
| $r_T$                  | On-state slope resistance                  |  |                         |       |      | 3.01 | $\text{m}\Omega$               |
| $V_{TM}$               | Peak on-state voltage                      | $I_{TM}=270\text{A}$   | 25                      |       |      | 1.80 | V                              |
| $dv/dt$                | Critical rate of rise of off-state voltage | $V_{DM}=67\%V_{DRM}$   | 125                     |       |      | 1000 | $\text{V}/\mu\text{s}$         |
| $di/dt$                | Critical rate of rise of on-state current  | Gate source 1.5A<br>$t_r \leq 0.5\mu\text{s}$ Repetitive                 | 125                     |       |      | 200  | $\text{A}/\mu\text{s}$         |
| $I_{GT}$               | Gate trigger current                       | $V_A=12\text{V}, I_A=1\text{A}$  | 25                      | 30    |      | 200  | mA                             |
| $V_{GT}$               | Gate trigger voltage                       |  |                         | 0.6   |      | 2.5  | V                              |
| $I_H$                  | Holding current                            |  |                         | 10    |      | 250  | mA                             |
| $V_{GD}$               | Non-trigger gate voltage                   | $V_{DM}=67\%V_{DRM}$   | 125                     |       |      | 0.2  | V                              |
| $R_{th(j-c)}$          | Thermal resistance<br>Junction to case     | Single side cooled per chip  |                         |       |      | 0.28 | $^{\circ}\text{C}/\text{W}$    |
| $R_{th(c-h)}$          | Thermal resistance<br>case to heatsink     | Single side cooled per chip  |                         |       |      | 0.15 | $^{\circ}\text{C}/\text{W}$    |
| $V_{iso}$              | Isolation voltage                          | 50Hz, R.M.S, $t=1\text{min}, I_{iso}: 1\text{mA}(\text{MAX})$            |                         | 3000  |      |      | V                              |
| $F_m$                  | Thermal connection torque(M5)              |  |                         | 2.5   |      | 4.0  | N·m                            |
|                        | Mounting torque(M6)                        |  |                         | 4.5   |      | 6.0  | N·m                            |
| $T_{vj}$               | Junction temperature                       |  |                         | -40   |      | 125  | $^{\circ}\text{C}$             |
| $T_{stg}$              | Stored temperature                         |  |                         | -40   |      | 125  | $^{\circ}\text{C}$             |
| $W_t$                  | Weight                                     |  |                         |       | 100  |      | g                              |
| Outline                | 224H3                                      |  |                         |       |      |      |                                |

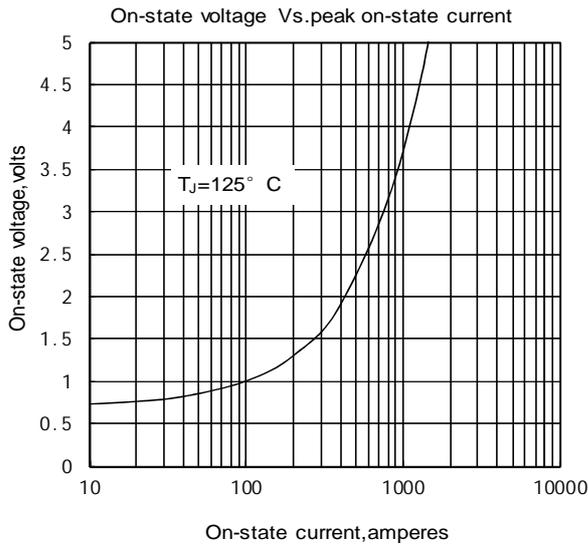


Fig1

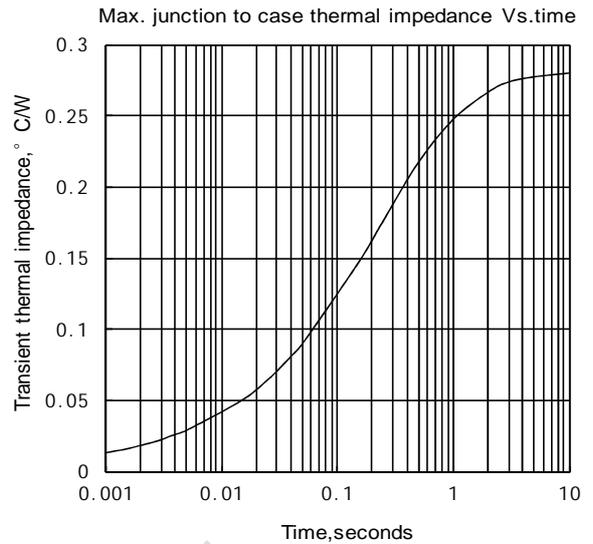


Fig2

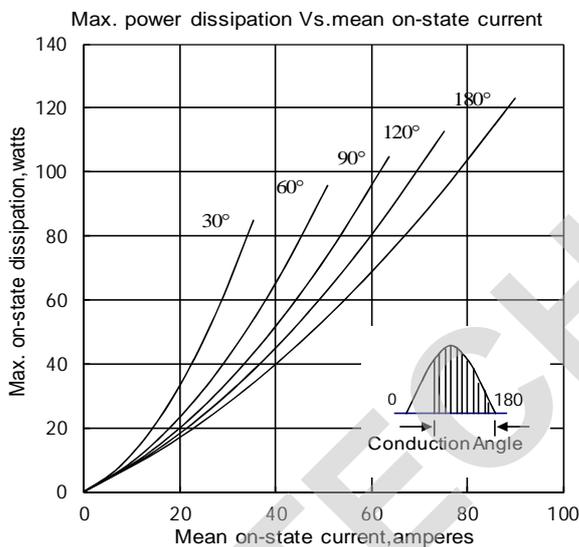


Fig3

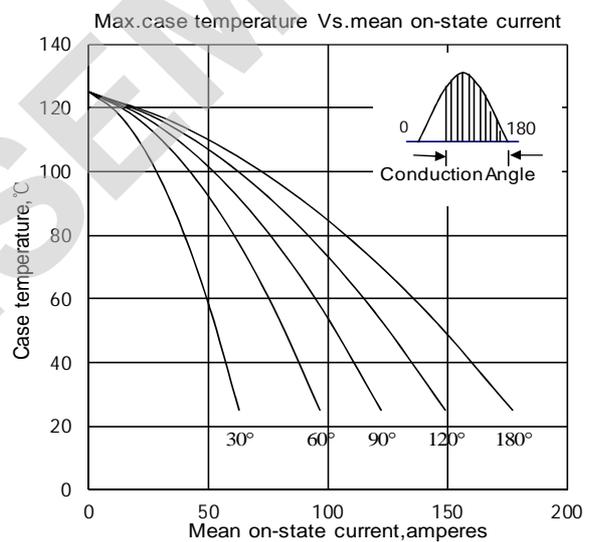


Fig4

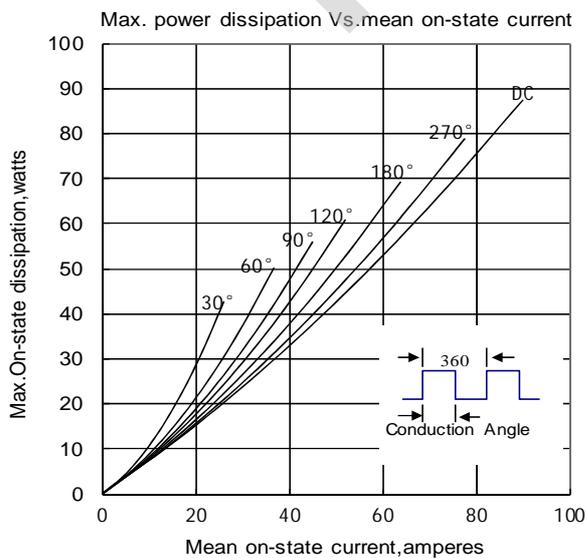


Fig5

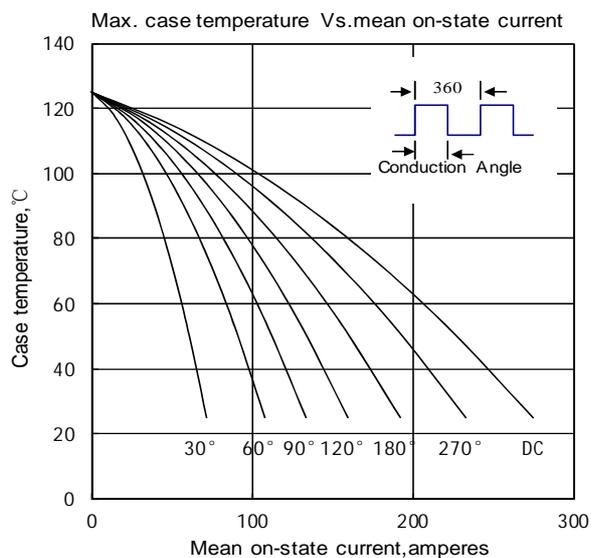


Fig6

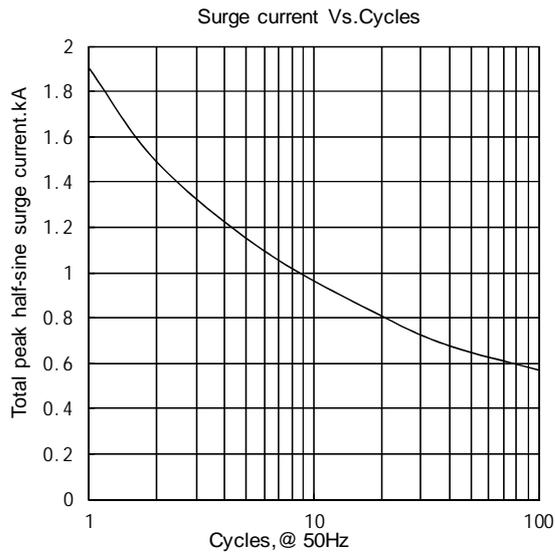


Fig7

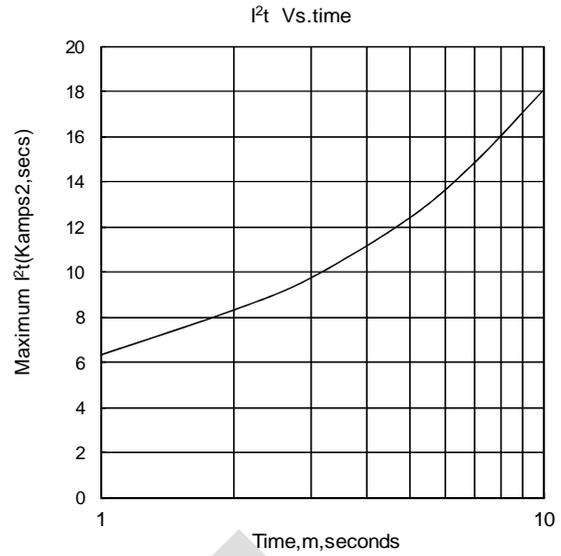
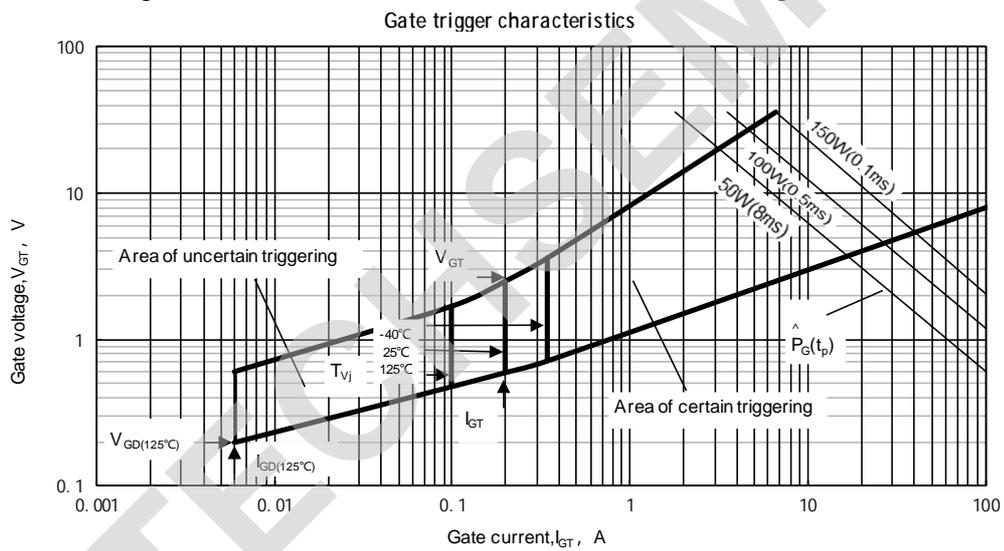


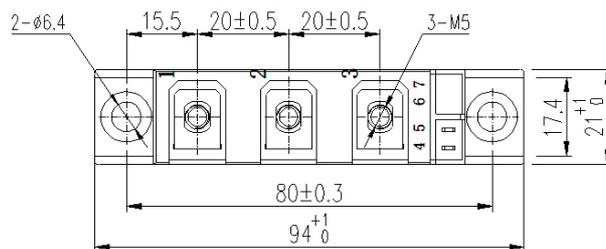
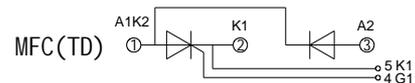
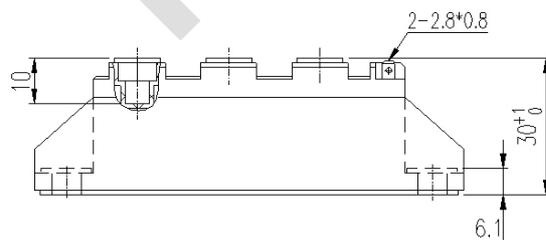
Fig8



Gate trigger characteristics

Fig.9

Outline:



Unmarked dimensional tolerance:  $\pm 0.5\text{mm}$

TECHSEM reserves the right to change specifications without notice.